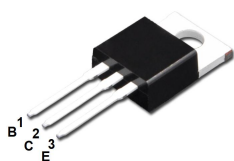
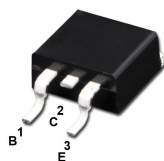


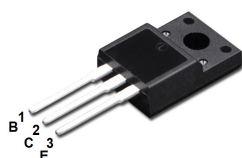
NPN Silicon Epitaxial Planar Transistor



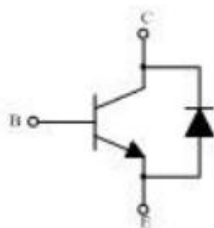
TO-220AB/SL13005AB



TO-263/SL13005AK



TO-220F/SL13005AF



FEATURES

- High voltage
- High speed switching

APPLICATIONS

- High Speed Switching
- Suitable for Switching Regulator and Motor Control



MECHANICAL DATA

- **Case:** Molded plastic
- **Polarity:** As marked
- **Mounting Position:** Any
- **Molded Plastic:** UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275°C maximum, 10s per JESD 22-B106

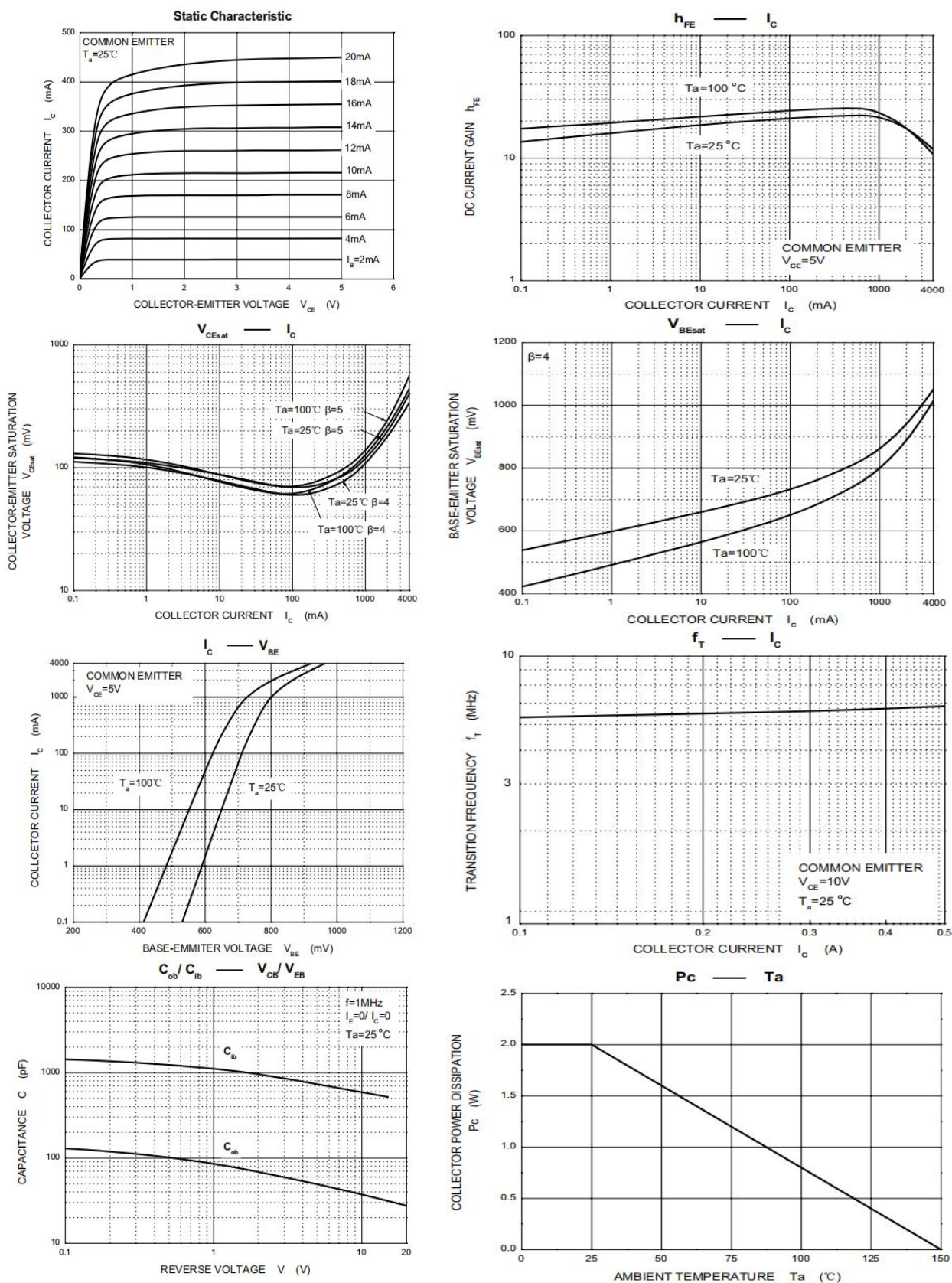
Maximum Ratings at Ta=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	800	V
Collector Emitter Voltage	V_{CEO}	450	V
Emitter Base Voltage	V_{EBO}	9	V
Collector Current	I_C	4	A
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Power Dissipation (Tc = 25 °C) Superimposed on Rated Load (JEDEC method)	P_{tot}	1.25	W
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Electrical Characteristics(Ta=25°C)

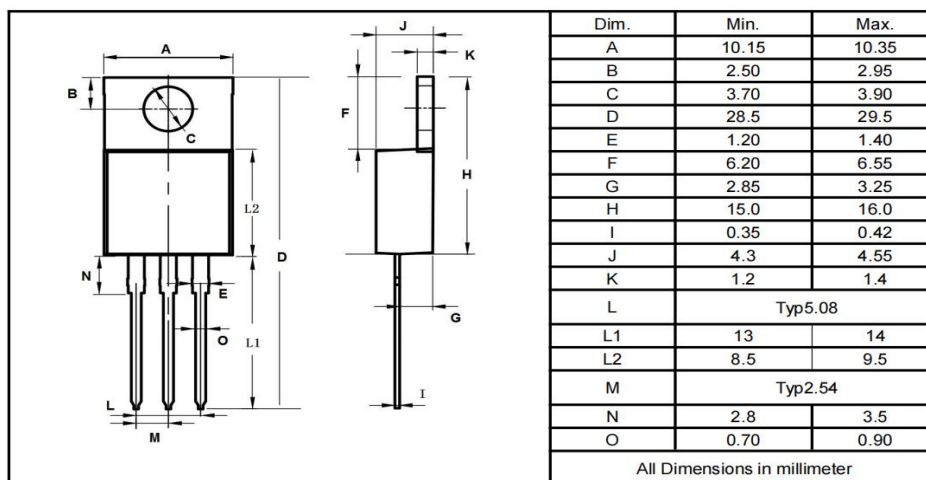
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5V$, $I_C = 1A$	h_{FE}	15	-	35	-
Collector Base Cutoff Current at $V_{CB} = 750V$	I_{CBO}	-	-	10	μA
Collector Emitter Cutoff Current at $V_{CE} = 400V$	I_{CEO}	-	-	10	μA
Emitter Base Cutoff Current at $V_{EB} = 9V$	I_{EBO}	-	-	10	μA
Collector Emitter Saturation Voltage at $I_C = 200mA$, $I_B = 40mA$	$V_{CE(sat)}$	-	-	1	V
Base Emitter Saturation Voltage at $I_C = 200mA$, $I_B = 40mA$	$V_{BE(sat)}$	-	-	1.5	V
Transition Frequency at $V_{CE}=10V$, $I_C=500mA$, $f=1MHz$	f_T	4	-	-	MHZ

RATINGS AND CHARACTERISTIC CURVES

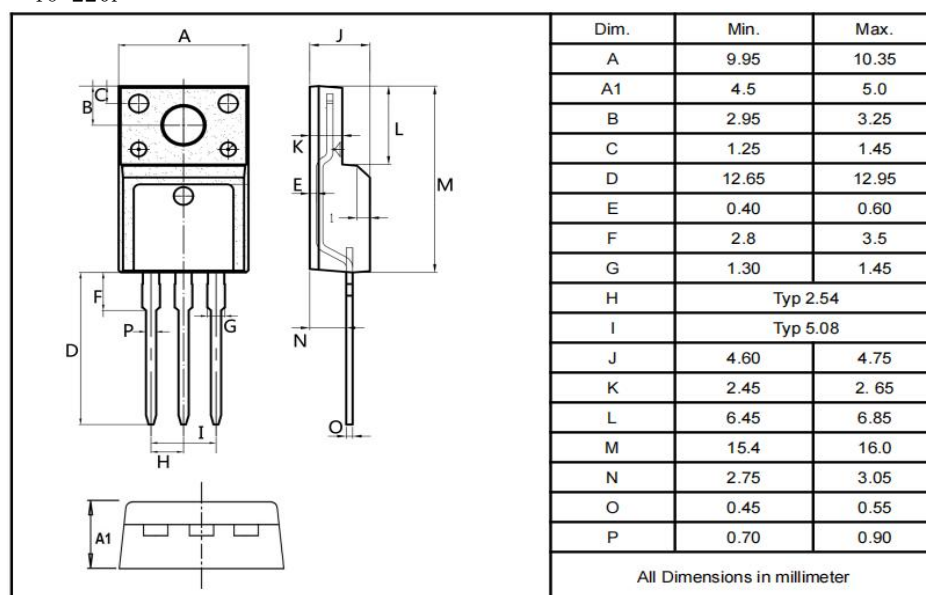


Package Outline Dimensions millimeters

T0-220AB



T0-220F



T0-263

